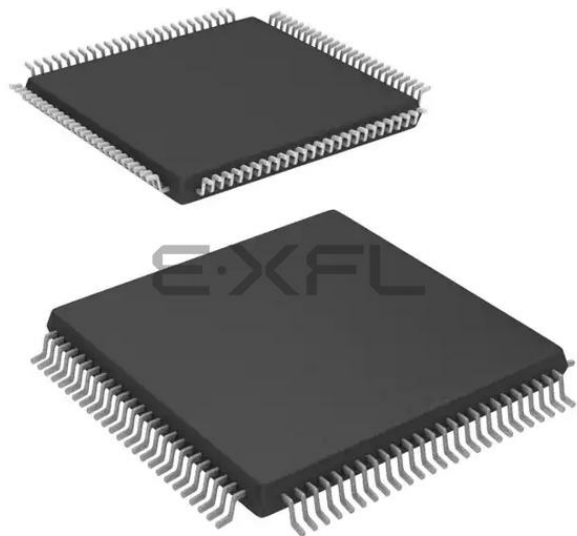




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	768
Total RAM Bits	-
Number of I/O	77
Number of Gates	30000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/agln030v2-zvqg100

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-19 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-20 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-20 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption— P_{TOTAL}

$$P_{TOTAL} = P_{STAT} + P_{DYN}$$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption— P_{STAT}

$$P_{STAT} = (PDC1 \text{ or } PDC2 \text{ or } PDC3) + N_{BANKS} * PDC5$$

N_{BANKS} is the number of I/O banks powered in the design.

Total Dynamic Power Consumption— P_{DYN}

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

Global Clock Contribution— P_{CLOCK}

$$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S-CELL} * PAC4) * F_{CLK}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the *IGLOO nano FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the *IGLOO nano FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution— P_{S-CELL}

$$P_{S-CELL} = N_{S-CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-19 on page 2-14.

F_{CLK} is the global clock signal frequency.

User I/O Characteristics

Timing Model

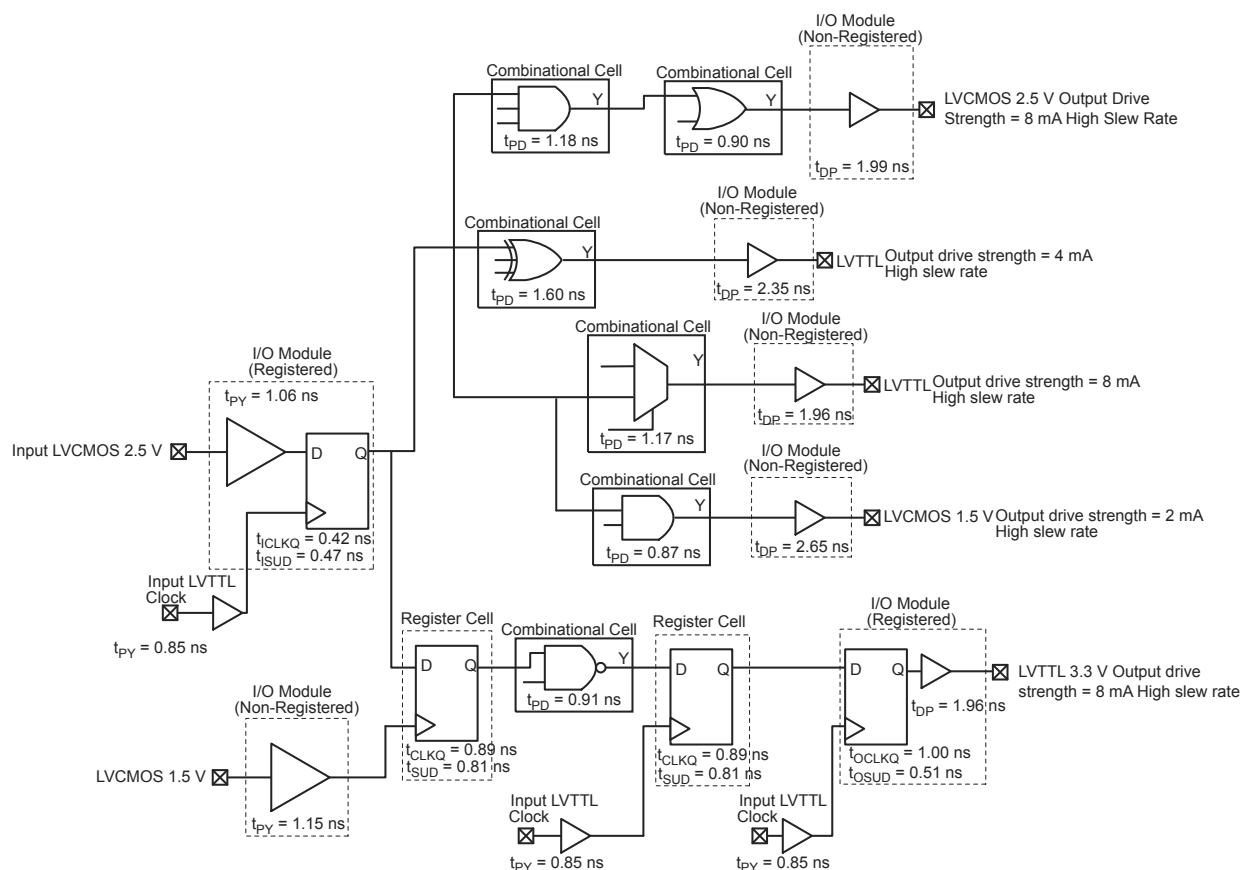


Figure 2-3 • Timing Model

Operating Conditions: STD Speed, Commercial Temperature Range ($T_J = 70^\circ\text{C}$), Worst-Case $V_{CC} = 1.425$ V, for DC 1.5 V Core Voltage, Applicable to V2 and V5 Devices

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels
Applicable to Commercial and Industrial Conditions—Software Default Settings

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength ²	Slew Rate	VIL		VIH		VOL	VOH	IOL ¹	IOH ¹
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8 mA	High	−0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range ³	100 μ A	8 mA	High	−0.3	0.8	2	3.6	0.2	VCCI − 0.2	100 μ A	100 μ A
2.5 V LVCMOS	8 mA	8 mA	High	−0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS ⁴	1 mA	1 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1
1.2 V LVCMOS Wide Range ^{4,5}	100 μ A	1 mA	High	−0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI − 0.1	100 μ A	100 μ A

Notes:

1. Currents are measured at 85°C junction temperature.
2. The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \mu$ A. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification.
4. Applicable to IGLOO nano V2 devices operating at VCCI $\geq$ VCC.
5. All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range, as specified in the JESD8-12 specification.

Table 2-22 • Summary of Maximum and Minimum DC Input Levels
Applicable to Commercial and Industrial Conditions

DC I/O Standards	Commercial ¹		Industrial ²	
	IIL ³	IIH ⁴	IIL ³	IIH ⁴
	μ A	μ A	μ A	μ A
3.3 V LVTTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCOMS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
1.2 V LVCMOS ⁵	10	10	15	15
1.2 V LVCMOS Wide Range ⁵	10	10	15	15

Notes:

1. Commercial range ($-20^{\circ}\text{C} < T_A < 70^{\circ}\text{C}$)
2. Industrial range ($-40^{\circ}\text{C} < T_A < 85^{\circ}\text{C}$)
3. I_{IH} is the input leakage current per I/O pin over recommended operating conditions, where $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
4. I_{IL} is the input leakage current per I/O pin over recommended operating conditions, where $-0.3 \text{ V} < V_{IN} < V_{IL}$.
5. Applicable to IGLOO nano V2 devices operating at VCCI $\geq$ VCC.

Applies to IGLOO nano at 1.2 V Core Operating Conditions

Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings
STD Speed Grade, Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$,
Worst-Case $V_{CCI} = 3.0\text{ V}$

I/O Standard	Drive Strength (mA)	Equiv. Software Default Drive Strength Option ¹	Slew Rate	Capacitive Load (pF)	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8 mA	High	5 pF	1.55	2.31	0.26	0.97	1.36	1.10	2.34	1.90	2.43	3.14	ns
3.3 V LVCMOS Wide Range ²	100 μA	8 mA	High	5 pF	1.55	3.25	0.26	1.31	1.91	1.10	3.25	2.61	3.38	4.27	ns
2.5 V LVCMOS	8 mA	8 mA	High	5 pF	1.55	2.30	0.26	1.21	1.39	1.10	2.33	2.04	2.41	2.99	ns
1.8 V LVCMOS	4 mA	4 mA	High	5 pF	1.55	2.49	0.26	1.13	1.59	1.10	2.53	2.34	2.42	2.81	ns
1.5 V LVCMOS	2 mA	2 mA	High	5 pF	1.55	2.78	0.26	1.27	1.77	1.10	2.82	2.62	2.44	2.74	ns
1.2 V LVCMOS	1 mA	1 mA	High	5 pF	1.55	3.50	0.26	1.56	2.27	1.10	3.37	3.10	2.55	2.66	ns
1.2 V LVCMOS Wide Range ³	100 μA	1 mA	High	5 pF	1.55	3.50	0.26	1.56	2.27	1.10	3.37	3.10	2.55	2.66	ns

Notes:

1. The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification.
3. All LVCMOS 1.2 V software macros support LVCMOS 1.2 V side range as specified in the JESD8-12 specification.
4. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Applies to 1.2 V DC Core Voltage

Table 2-43 • 3.3 V LVC MOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$, Worst-Case $V_{CCI} = 2.7\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 μA	2 mA	STD	1.55	6.01	0.26	1.31	1.91	1.10	6.01	5.66	3.02	3.49	ns
100 μA	4 mA	STD	1.55	6.01	0.26	1.31	1.91	1.10	6.01	5.66	3.02	3.49	ns
100 μA	6 mA	STD	1.55	5.02	0.26	1.31	1.91	1.10	5.02	4.76	3.38	4.10	ns
100 μA	8 mA	STD	1.55	5.02	0.26	1.31	1.91	1.10	5.02	4.76	3.38	4.10	ns

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-44 • 3.3 V LVC MOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$, Worst-Case $V_{CCI} = 2.7\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 μA	2 mA	STD	1.55	3.82	0.26	1.31	1.91	1.10	3.82	3.15	3.01	3.65	ns
100 μA	4 mA	STD	1.55	3.82	0.26	1.31	1.91	1.10	3.82	3.15	3.01	3.65	ns
100 μA	6 mA	STD	1.55	3.25	0.26	1.31	1.91	1.10	3.25	2.61	3.38	4.27	ns
100 μA	8 mA	STD	1.55	3.25	0.26	1.31	1.91	1.10	3.25	2.61	3.38	4.27	ns

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.
3. Software default selection highlighted in gray.

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-51 • Minimum and Maximum DC Input and Output Levels

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	I _{IH} ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	2	2	9	11	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	4	4	17	22	10	10

Notes:

1. I_{IL} is the input leakage current per I/O pin over recommended operating conditions where $-0.3 < V_{IN} < V_{IL}$.
2. I_{IH} is the input leakage current per I/O pin over recommended operating conditions where $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

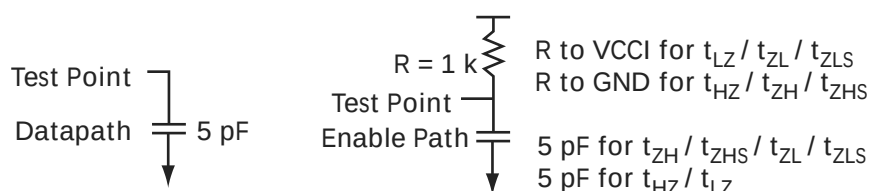


Figure 2-9 • AC Loading

Table 2-52 • 1.8 V LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads

Input LOW (V)	Input HIGH (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.8	0.9	5

Note: *Measuring point = V_{trip} . See Table 2-23 on page 2-20 for a complete table of trip points.

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-57 • Minimum and Maximum DC Input and Output Levels

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10

Notes:

1. I_{IL} is the input leakage current per I/O pin over recommended operating conditions where $-0.3 < V_{IN} < V_{IL}$.
2. I_{IH} is the input leakage current per I/O pin over recommended operating conditions where $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

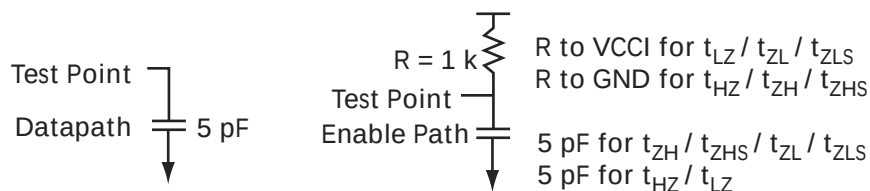


Figure 2-10 • AC Loading

Table 2-58 • 1.5 V LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads

Input LOW (V)	Input HIGH (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.5	0.75	5

Note: *Measuring point = V_{trip} . See Table 2-23 on page 2-20 for a complete table of trip points.

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-59 • 1.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	5.39	0.19	1.19	1.62	0.66	5.48	5.39	2.02	2.06	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-60 • 1.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	2.39	0.19	1.19	1.62	0.66	2.44	2.24	2.02	2.15	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Applies to 1.2 V DC Core Voltage

Table 2-61 • 1.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	1.55	5.87	0.26	1.27	1.77	1.10	5.92	5.87	2.45	2.65	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-62 • 1.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	1.55	2.78	0.26	1.27	1.77	1.10	2.82	2.62	2.44	2.74	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V LVCMOS (JESD8-12A)

Low-Voltage CMOS for 1.2 V complies with the LVCMOS standard JESD8-12A for general purpose 1.2 V applications. It uses a 1.2 V input buffer and a push-pull output buffer.

Table 2-63 • Minimum and Maximum DC Input and Output Levels

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
1 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1	10	13	10	10

Notes:

1. I_{IL} is the input leakage current per I/O pin over recommended operating conditions where $-0.3 < V_{IN} < V_{IL}$.
2. I_{IH} is the input leakage current per I/O pin over recommended operating conditions where $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

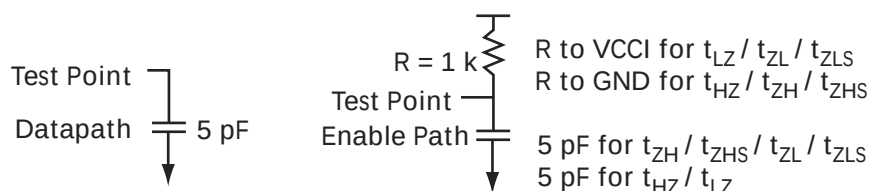


Figure 2-11 • AC Loading

Table 2-64 • 1.2 V LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads

Input LOW (V)	Input HIGH (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.2	0.6	5

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.

Timing Characteristics

Applies to 1.2 V DC Core Voltage

Table 2-65 • 1.2 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
1 mA	STD	1.55	8.30	0.26	1.56	2.27	1.10	7.97	7.54	2.56	2.55	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-66 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
1 mA	STD	1.55	3.50	0.26	1.56	2.27	1.10	3.37	3.10	2.55	2.66	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-70 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-12 on page 2-41 for more information.

1.2 V DC Core Voltage

Table 2-73 • Input Data Register Propagation Delays
Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Input Data Register	0.68	ns
t_{SUD}	Data Setup Time for the Input Data Register	0.97	ns
t_{HD}	Data Hold Time for the Input Data Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	1.19	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	1.19	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
t_{CKMPWH}	Clock Minimum Pulse Width HIGH for the Input Data Register	0.31	ns
t_{CKMPWL}	Clock Minimum Pulse Width LOW for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Global Resource Characteristics

AGLN125 Clock Tree Topology

Clock delays are device-specific. Figure 2-25 is an example of a global tree used for clock routing. The global tree presented in Figure 2-25 is driven by a CCC located on the west side of the AGLN125 device. It is used to drive all D-flip-flops in the device.

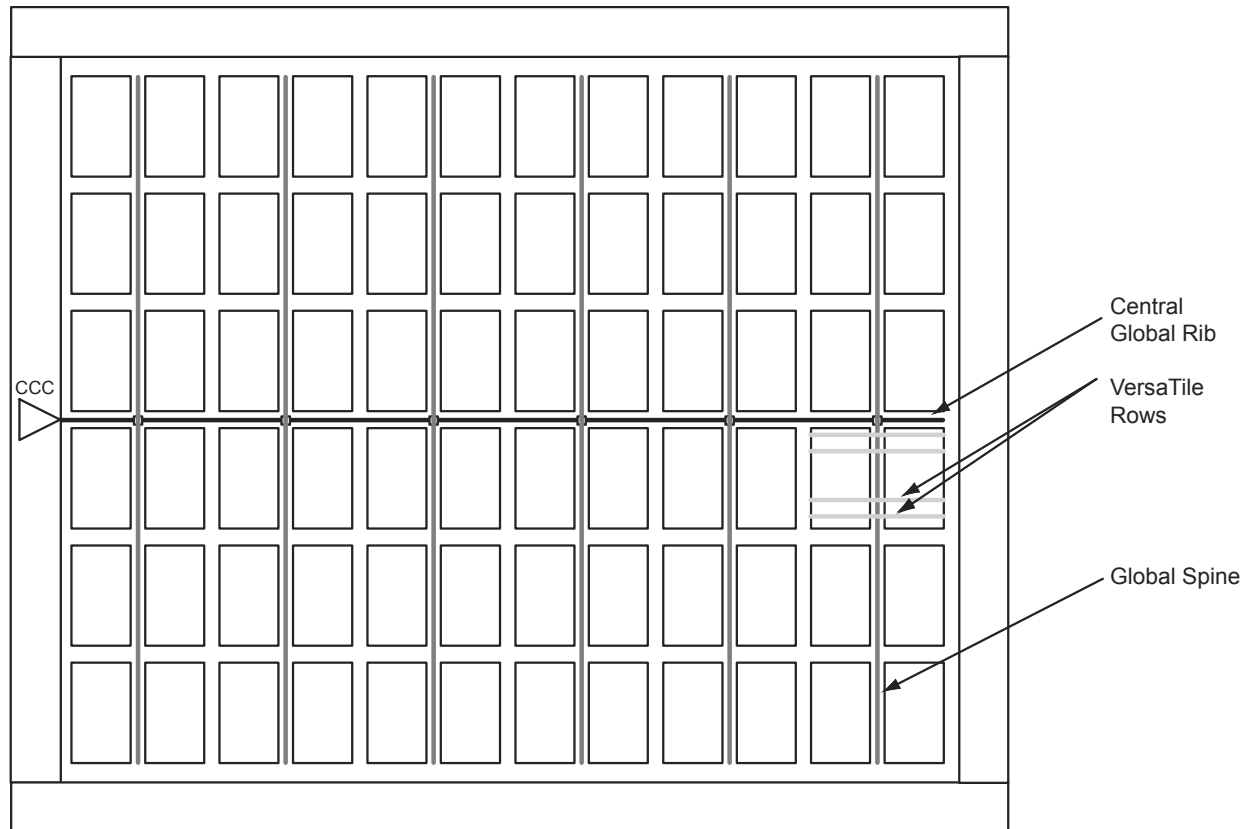
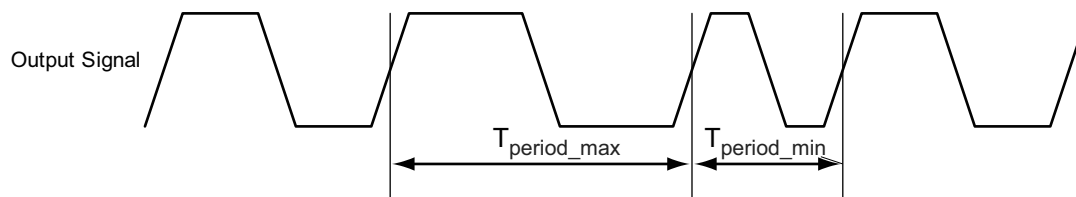


Figure 2-25 • Example of Global Tree Use in an AGLN125 Device for Clock Routing



Note: Peak-to-peak jitter measurements are defined by $T_{\text{peak-to-peak}} = T_{\text{period_max}} - T_{\text{period_min}}$.

Figure 2-26 • Peak-to-Peak Jitter Definition

FIFO

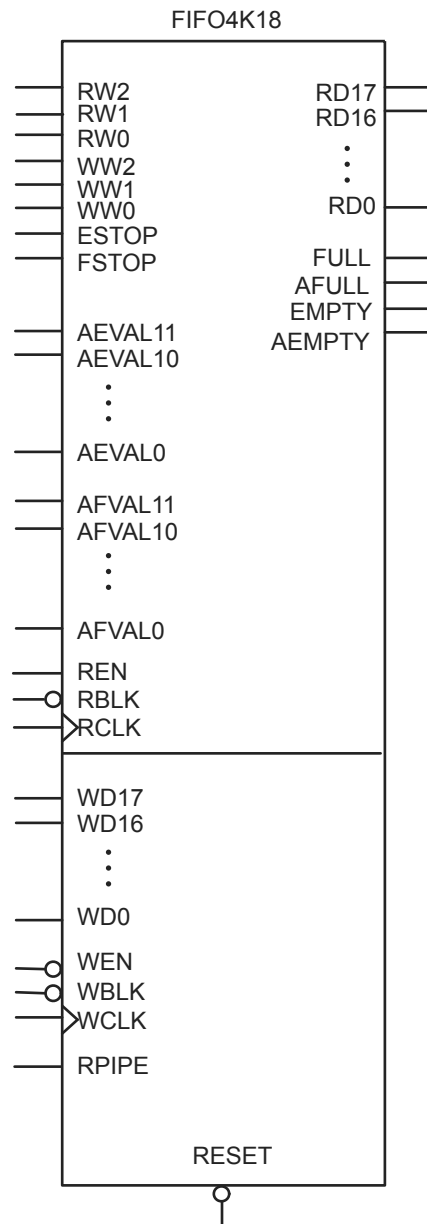


Figure 2-33 • FIFO Model

3 – Pin Descriptions

Supply Pins

GND **Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ **Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC **Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V for IGLOO nano V5 devices, and 1.2 V or 1.5 V for IGLOO nano V2 devices. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

VCCIBx **I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.2 V, 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VCCI pins tied to GND.

VMVx **I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. x is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.2 V, 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F **PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V or 1.2 V.

When the PLLs are not used, the Microsemi Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter in the *IGLOO nano FPGA Fabric User's Guide* for a complete board solution for the PLL analog power supply and ground.

There is one VCCPLF pin on IGLOO nano devices.

VCOMPLA/B/C/D/E/F **PLL Ground**

Ground to analog PLL power supplies. When the PLLs are not used, the Microsemi Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There is one VCOMPLF pin on IGLOO nano devices.

VJTAG **JTAG Supply Voltage**

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG

CS81		CS81		CS81	
Pin Number	AGLN020 Function	Pin Number	AGLN020 Function	Pin Number	AGLN020 Function
A1	IO64RSB2	E1	GEC0/IO48RSB2	J1	IO38RSB1
A2	IO54RSB2	E2	GEA0/IO47RSB2	J2	IO37RSB1
A3	IO57RSB2	E3	NC	J3	IO33RSB1
A4	IO36RSB1	E4	VCCIB1	J4	IO30RSB1
A5	IO32RSB1	E5	VCC	J5	IO27RSB1
A6	IO24RSB1	E6	VCCIB0	J6	IO23RSB1
A7	IO20RSB1	E7	NC	J7	TCK
A8	IO04RSB0	E8	GDA0/IO15RSB0	J8	TMS
A9	IO08RSB0	E9	GDC0/IO14RSB0	J9	VPUMP
B1	IO59RSB2	F1	IO46RSB2		
B2	IO55RSB2	F2	IO45RSB2		
B3	IO62RSB2	F3	NC		
B4	IO34RSB1	F4	GND		
B5	IO28RSB1	F5	VCCIB1		
B6	IO22RSB1	F6	NC		
B7	IO18RSB1	F7	NC		
B8	IO00RSB0	F8	IO16RSB0		
B9	IO03RSB0	F9	IO17RSB0		
C1	IO51RSB2	G1	IO43RSB2		
C2	IO50RSB2	G2	IO42RSB2		
C3	NC	G3	IO41RSB2		
C4	NC	G4	IO31RSB1		
C5	NC	G5	NC		
C6	NC	G6	IO21RSB1		
C7	NC	G7	NC		
C8	IO10RSB0	G8	VJTAG		
C9	IO07RSB0	G9	TRST		
D1	IO49RSB2	H1	IO40RSB2		
D2	IO44RSB2	H2	FF/IO39RSB1		
D3	NC	H3	IO35RSB1		
D4	VCC	H4	IO29RSB1		
D5	VCCIB2	H5	IO26RSB1		
D6	GND	H6	IO25RSB1		
D7	NC	H7	IO19RSB1		
D8	IO13RSB0	H8	TDI		
D9	IO12RSB0	H9	TDO		

CS81		CS81		CS81	
Pin Number	AGLN060 Function	Pin Number	AGLN060 Function	Pin Number	AGLN060 Function
A1	GAA0/IO02RSB0	D8	GCC1/IO35RSB0	H6	IO56RSB1
A2	GAA1/IO03RSB0	D9	GCC0/IO36RSB0	H7 ²	GDA2/IO51RSB1
A3	GAC0/IO06RSB0	E1	GFB0/IO83RSB1	H8	TDI
A4	IO09RSB0	E2	GFB1/IO84RSB1	H9	TDO
A5	IO13RSB0	E3	GFA1/IO81RSB1	J1	GEA2/IO68RSB1
A6	IO18RSB0	E4	VCCIB1	J2	GEC2/IO66RSB1
A7	GBB0/IO21RSB0	E5	VCC	J3	IO64RSB1
A8	GBA1/IO24RSB0	E6	VCCIB0	J4	IO61RSB1
A9	GBA2/IO25RSB0	E7	GCA1/IO39RSB0	J5	IO58RSB1
B1	GAA2/IO95RSB1	E8	GCA0/IO40RSB0	J6	IO55RSB1
B2	GAB0/IO04RSB0	E9	GCB2/IO42RSB0	J7	TCK
B3	GAC1/IO07RSB0	F1 ¹	VCCPLF	J8	TMS
B4	IO08RSB0	F2 ¹	VCOMPLF	J9	VPUMP
B5	IO15RSB0	F3	GND		
B6	GBC0/IO19RSB0	F4	GND		
B7	GBB1/IO22RSB0	F5	VCCIB1		
B8	IO26RSB0	F6	GND		
B9	GBB2/IO27RSB0	F7	GDA1/IO49RSB0		
C1	GAB2/IO93RSB1	F8	GDC1/IO45RSB0		
C2	IO94RSB1	F9	GDC0/IO46RSB0		
C3	GND	G1	GEA0/IO69RSB1		
C4	IO10RSB0	G2	GEC1/IO74RSB1		
C5	IO17RSB0	G3	GEB1/IO72RSB1		
C6	GND	G4	IO63RSB1		
C7	GBA0/IO23RSB0	G5	IO60RSB1		
C8	GBC2/IO29RSB0	G6	IO54RSB1		
C9	IO31RSB0	G7	GDB2/IO52RSB1		
D1	GAC2/IO91RSB1	G8	VJTAG		
D2	IO92RSB1	G9	TRST		
D3	GFA2/IO80RSB1	H1	GEA1/IO70RSB1		
D4	VCC	H2	FF/GEB2/IO67RSB1		
D5	VCCIB0	H3	IO65RSB1		
D6	GND	H4	IO62RSB1		
D7	GCC2/IO43RSB0	H5	IO59RSB1		

Notes:

1. Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN060-CS81.
2. The bus hold attribute (hold previous I/O state in Flash*Freeze mode) is not supported for pin H7 in AGLN060-CS81.

CS81	
Pin Number	AGLN060Z Function
A1	GAA0/IO02RSB0
A2	GAA1/IO03RSB0
A3	GAC0/IO06RSB0
A4	IO09RSB0
A5	IO13RSB0
A6	IO18RSB0
A7	GBB0/IO21RSB0
A8	GBA1/IO24RSB0
A9	GBA2/IO25RSB0
B1	GAA2/IO95RSB1
B2	GAB0/IO04RSB0
B3	GAC1/IO07RSB0
B4	IO08RSB0
B5	IO15RSB0
B6	GBC0/IO19RSB0
B7	GBB1/IO22RSB0
B8	IO26RSB0
B9	GBB2/IO27RSB0
C1	GAB2/IO93RSB1
C2	IO94RSB1
C3	GND
C4	IO10RSB0
C5	IO17RSB0
C6	GND
C7	GBA0/IO23RSB0
C8	GBC2/IO29RSB0
C9	IO31RSB0
D1	GAC2/IO91RSB1
D2	IO92RSB1
D3	GFA2/IO80RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	GCC2/IO43RSB0

CS81	
Pin Number	AGLN060Z Function
D8	GCC1/IO35RSB0
D9	GCC0/IO36RSB0
E1	GFB0/IO83RSB1
E2	GFB1/IO84RSB1
E3	GFA1/IO81RSB1
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	GCA1/IO39RSB0
E8	GCA0/IO40RSB0
E9	GCB2/IO42RSB0
F1 ¹	VCCPLF
F2 ¹	VCOMPLF
F3	GND
F4	GND
F5	VCCIB1
F6	GND
F7	GDA1/IO49RSB0
F8	GDC1/IO45RSB0
F9	GDC0/IO46RSB0
G1	GEA0/IO69RSB1
G2	GEC1/IO74RSB1
G3	GEB1/IO72RSB1
G4	IO63RSB1
G5	IO60RSB1
G6	IO54RSB1
G7	GDB2/IO52RSB1
G8	VJTAG
G9	TRST
H1	GEA1/IO70RSB1
H2	FF/GEB2/IO67RSB1
H3	IO65RSB1
H4	IO62RSB1
H5	IO59RSB1

CS81	
Pin Number	AGLN060Z Function
H6	IO56RSB1
H7 ²	GDA2/IO51RSB1
H8	TDI
H9	TDO
J1	GEA2/IO68RSB1
J2	GEC2/IO66RSB1
J3	IO64RSB1
J4	IO61RSB1
J5	IO58RSB1
J6	IO55RSB1
J7	TCK
J8	TMS
J9	VPUMP

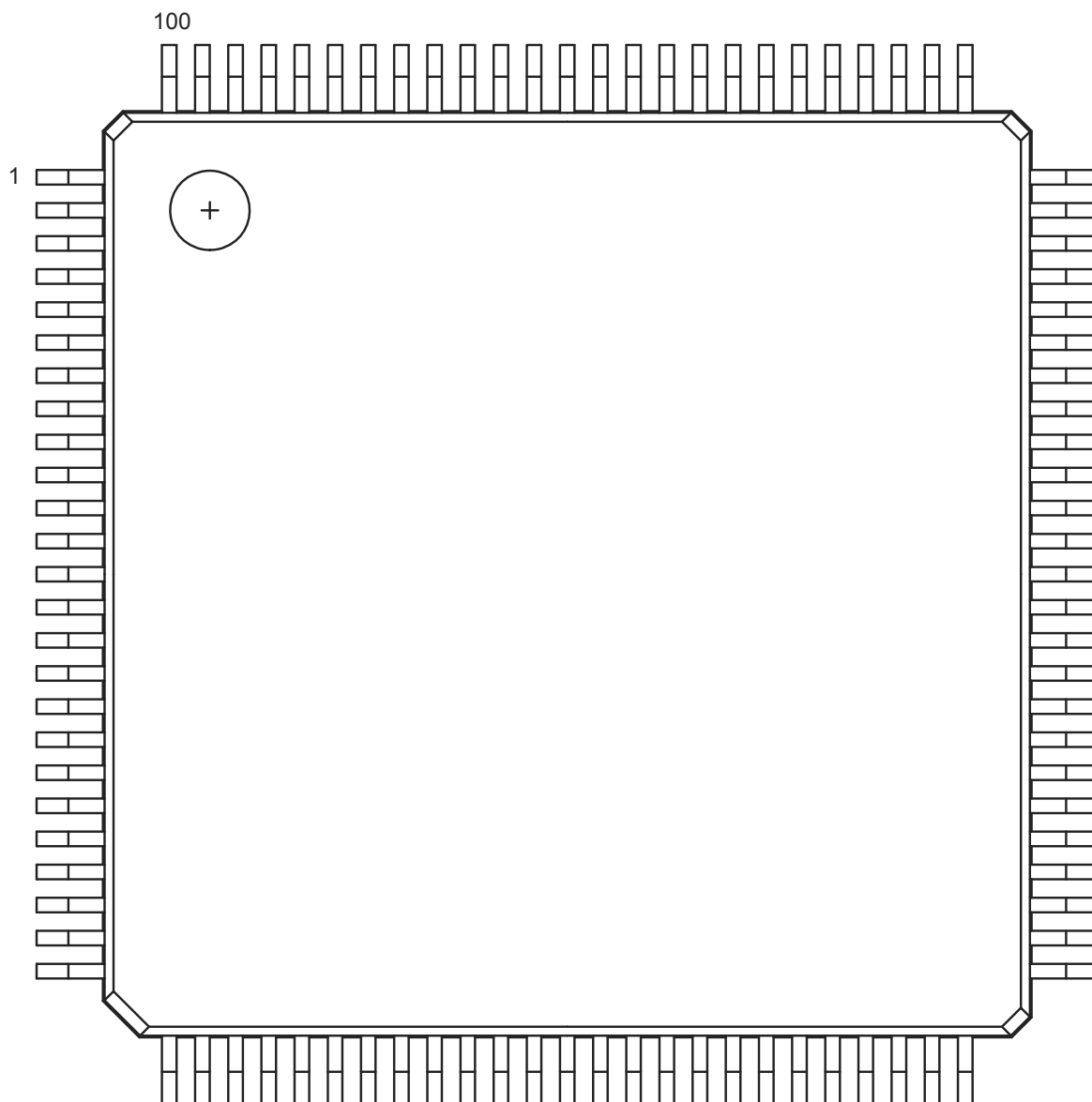
Notes:

1. Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN060Z-CS81.
2. The bus hold attribute (hold previous I/O state in Flash*Freeze mode) is not supported for pin H7 in AGLN060Z-CS81.

CS81		CS81		CS81	
Pin Number	AGLN125 Function	Pin Number	AGLN125 Function	Pin Number	AGLN125 Function
A1	GAA0/IO00RSB0	E1	GFB0/IO120RSB1	J1	GEA2/IO103RSB1
A2	GAA1/IO01RSB0	E2	GFB1/IO121RSB1	J2	GEC2/IO101RSB1
A3	GAC0/IO04RSB0	E3	GFA1/IO118RSB1	J3	IO97RSB1
A4	IO13RSB0	E4	VCCIB1	J4	IO93RSB1
A5	IO22RSB0	E5	VCC	J5	IO90RSB1
A6	IO32RSB0	E6	VCCIB0	J6	IO78RSB1
A7	GBB0/IO37RSB0	E7	GCA0/IO56RSB0	J7	TCK
A8	GBA1/IO40RSB0	E8	GCA1/IO55RSB0	J8	TMS
A9	GBA2/IO41RSB0	E9	GCB2/IO58RSB0	J9	VPUMP
B1	GAA2/IO132RSB1	F1*	VCCPLF		
B2	GAB0/IO02RSB0	F2*	VCOMPLF		
B3	GAC1/IO05RSB0	F3	GND		
B4	IO11RSB0	F4	GND		
B5	IO25RSB0	F5	VCCIB1		
B6	GBC0/IO35RSB0	F6	GND		
B7	GBB1/IO38RSB0	F7	GDA1/IO65RSB0		
B8	IO42RSB0	F8	GDC1/IO61RSB0		
B9	GBB2/IO43RSB0	F9	GDC0/IO62RSB0		
C1	GAB2/IO130RSB1	G1	GEA0/IO104RSB1		
C2	IO131RSB1	G2	GEC0/IO108RSB1		
C3	GND	G3	GEB1/IO107RSB1		
C4	IO15RSB0	G4	IO96RSB1		
C5	IO28RSB0	G5	IO92RSB1		
C6	GND	G6	IO72RSB1		
C7	GBA0/IO39RSB0	G7	GDB2/IO68RSB1		
C8	GBC2/IO45RSB0	G8	VJTAG		
C9	IO47RSB0	G9	TRST		
D1	GAC2/IO128RSB1	H1	GEA1/IO105RSB1		
D2	IO129RSB1	H2	FF/GEB2/IO102RSB1		
D3	GFA2/IO117RSB1	H3	IO99RSB1		
D4	VCC	H4	IO94RSB1		
D5	VCCIB0	H5	IO91RSB1		
D6	GND	H6	IO81RSB1		
D7	GCC2/IO59RSB0	H7	GDA2/IO67RSB1		
D8	GCC1/IO51RSB0	H8	TDI		
D9	GCC0/IO52RSB0	H9	TDO		

Note: * Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN125-CS81.

VQ100



Note: This is the top view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>.